

Tetsuhiro NAKAMURA

Docket No. 020264

REMARKS

The above amendment is submitted to place the claims in substantially the same conditions as to the claims which have been amended under Article 34 in the international application and to remove improper multiple dependency of the claims. An English translation of the annexes of the PCT international preliminary examination report is enclosed. Early and favorable action is awaited.

Attached hereto is a marked-up version of the changes made to the claims by the current amendment. The attached page is captioned "Version with marking to show changes made."

In the event there are any additional fees required, please charge our Deposit Account No. 01-2340.

Respectfully submitted,

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Tetsuhiro NAKAMURA

Docket No. 020264

VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

The following claims have been amended as follows:

The following claims have been amended as follows:

1.(Amended) An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on part of the surface of an object to be plated, or causing the metal to be in contact with part of the surface of the object to be plated, made of a constituent material to which an electroless plating can not be applied; and

dipping the object to be plated having said metallic film formed thereon or having said metal in contact therewith in an electroless plating bath, and forming an electroless plating film on the surface of the object to be plated, without the metallic film formed thereon and the metal in contact therewith.

3. (Amended) An electroless plating method [according to claims 1 or 2, ] comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on part of the surface of an object to be plated, or causing the metal to be in contact with part of the

Tetsuhiro NAKAMURA

Docket No. 020264

surface of the object to be plated, made of a constituent material to which an electroless plating can not be applied; and

dipping the object to be plated having the metallic film formed thereon or having the metal in contact therewith in an electroless plating bath,

wherein said object to be plated is made of plural kinds of constituent materials.

4. (Amended) An electroless plating method [according to claims 1 or 2,] comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on part of the surface of an object to be plated, or causing the metal to be in contact with part of the surface of the object to be plated, made of a constituent material to which an electroless plating can not be applied; and

dipping the object to be plated having the metallic film formed thereon or having the metal in contact therewith in an electroless plating bath, wherein said object to be plated is a thermoelectric semiconductor.

6. (Amended) An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on one of end faces of a thermoelectric device block formed integrally with a plurality of [bar-shaped] thermoelectric semiconductors, disposed with an insulation layer interposed therebetween, respectively;

Tetsuhiro NAKAMURA

Docket No. 020264

dipping said thermoelectric device block having the metallic film formed thereon in an electroless plating bath, and forming an electroless plating film on said metallic film and the other end face of the respective thermoelectric semiconductors, on the side thereof, opposite from the end face on which the metallic film is formed;

removing said metallic film and a portion of the electroless plating film covering up the metallic film; and

dipping again the thermoelectric device block subjected to the steps described above in the electroless plating bath, and forming an electroless plating film on the end face of the respective thermoelectric semiconductors from which the metallic film is removed.

7. (Amended) An electroless plating method comprising the steps of:

causing a metal on which an electroless plating film can be deposited to be in contact with a part of at least one of end faces of respective thermoelectric semiconductors of a thermoelectric device block formed integrally with a plurality of [bar-shaped] thermoelectric semiconductors, disposed with an insulation layer interposed therebetween, respectively;

dipping the thermoelectric device block having said metal in contact therewith in an electroless plating bath, and forming an electroless plating film on the entire surface of the respective thermoelectric semiconductors, except the part thereof, in contact with said metal,

separating the metal in contact with the respective thermoelectric semiconductors therefrom;  
and

dipping again the thermoelectric device block subjected to the steps described above in the electroless plating bath, and forming an electroless plating film on the part of the end faces of the respective thermoelectric semiconductors, in contact with said metal.

8. (Amended) An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on an end face of respective insulation layers disposed on the side of one of end faces of a thermoelectric device block formed integrally with a plurality of [bar-shaped] thermoelectric semiconductors, disposed with the respective insulation layers interposed therebetween, such that the metallic film spans said respective insulation layers and a portion of respective end faces of both the thermoelectric semiconductors adjacent to each other across the respective insulation layers alternately disposed; and

dipping the thermoelectric device block having said metallic film formed thereon in an electroless plating bath, and forming an electroless plating film on said metallic film and both end faces of the respective thermoelectric semiconductors with the metallic film formed on the portion of the end face thereof.

9. (Amended) An electroless plating method comprising the steps of:

forming a metallic film made of a metal on which an electroless plating film can be deposited on either an end face or the other end face of respective insulation layers, alternately, on the sides of both end faces of a thermoelectric device block formed integrally with a plurality of [bar-shaped]

Tetsuhiro NAKAMURA

Docket No. 020264

thermoelectric semiconductors, disposed with the respective insulation layers interposed therebetween, such that the metallic film spans the respective insulation layers and a portion of respective end faces of both the thermoelectric semiconductors adjacent to each other across the respective insulation layers; and

dipping the thermoelectric device block having said metallic film formed thereon in an electroless plating bath, and forming an electroless plating film on said metallic film and both end faces of the respective thermoelectric semiconductors with the metallic film formed on the portion of the end face and the other end face thereof.

10. (Amended) An electroless plating method according to [any one of claims 6 to 9] claim 6, wherein use is made of said thermoelectric device block provided with an exposed outer sidewall face of respective thermoelectric semiconductors positioned at opposite ends in the direction along which the respective thermoelectric semiconductors are arranged, and an electroless plating film is also formed on the exposed outer sidewall faces of respective thermoelectric semiconductors positioned at opposite ends as well in said step of forming the electroless plating film.

11. (Amended) An electroless plating method according to [any one of claims 6 to 9] claim 6, further comprising the step of rendering the end face of the thermoelectric device block into a rough surface prior to the step of forming the electroless plating film on said thermoelectric device block.

Tetsuhiro NAKAMURA

Docket No. 020264

12. (Amended) An electroless plating method according to [any one of claims 6 to 9] claim 6, further comprising the step of cleaning said thermoelectric device block before or after the step of forming the electroless plating film on said thermoelectric device block.